		Sheet I of I
U.S. Department of Commerce, Patent and Trademark Office	Application No.:	Unknown
	Filing Date:	Unknown
':	First Named Inventor:	Hamza Yilmaz
	Group Art Unit:	Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Examiner Name:	Unknown
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	Attorney Docket No.:	YMZ004 US

			U.S.	Patent Documents				
*Examiner Intials		Document Number	Date	Name	Class	Subclass		Date i
	1.	5,168,331	12/01/92	Yilmaz	257	331	-^-	
	2.	5,216,275	06/01/93	Chen	257	493		
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							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
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	<u> </u>	Other /	Art (Including Au	thor, Title, Date, Pertinent	Pages Etc.)			<u> </u>
					0 , ,			
	3.	Jongdae Kim et al., "High-Density Trench DMOSFETs Employing Two Step Trench Technique and Trench Contact Structure", ISPSD-2003 Proceedings, pp. 1-4						
	4.	Il-Yong Park et al., "Novel Process Techniques for Fabricating High Density Trench MOSFETs with Self-Aligned N ⁺ /P ⁺ Source Formed on the Trench Side Wall", ISPSD-2003 Proceedings, pp. 1-4.						
	5.		lt, et al., "Record	-low 4mΩ mm ² specific on				,
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	7.	Performance", ISPSD-2003 Proceedings, pp 1-4. Syotaro Ono et al., "30V New Fine Trench MOSFET with Ultra Low On-Resistance", ISPSD-2003 Proceedings, pp. 1-4.						
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* Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication with applicant.